Transistors

Low frequency transistor (for amplification) **2SD2696**

Structure

NPN Silicon Epitaxial Planar Transistor

Features

- 1) The transistor of 400mA class which went only with 2012 size conventionally is attained in 1208 size.
- 2) Collector saturation voltage is low. $V_{CE (sat)}$: max. 300mA at Ic = 100mA / IB = 2mA

Applications

Switching

Packaging specifications

	Package	Taping	
Туре	Code	T2L	
	Basic ordering unit (pieces)	8000	
2SD2696		0	

•Absolute maximum ratings (Ta=25°C)

Symbol	Limits	Unit
Vсво	30	V
VCEO	30	V
Vebo	6	V
lc	400	mA
ICP *1	800	mA
Po *2	150	mW / TOTAL
Tj	150	°C
Tstg	-55 to +150	°C
	VCBO VCEO VEBO Ic Icp *1 PD *2 Tj	VCBO 30 VCEO 30 VEBO 6 Ic 400 ICP *1 800 PD *2 150 Tj 150

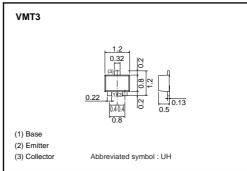
*1 Pw=10ms, Single pulse

*2 Each terminal mounted on a recommended land.

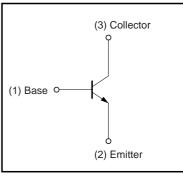
•Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-emitter breakdown voltage	BVCEO	30	-	-	V	Ic=1mA
Collector-base breakdown voltage	ВVсво	30	-	-	V	Ic=10µA
Emitter-base breakdown voltage	BVEBO	6	-	-	V	I _E =10μA
Collector cut-off current	Ісво	-	-	100	nA	V _{CB} = 30V
Emitter cut-off current	Іево	-	-	100	nA	VEB= 6V
Collector-emitter saturation voltage	VCE (sat)	-	120	300	mV	Ic=100mA, Iв= 2mA
DC current gain	hfe	270	-	680	-	Vce=2V, Ic=100mA
Transition frequency	f⊤	-	400	-	MHz	V _{CE} =2V, I _E = -100mA, f=100MHz
Output capacitance	Cob	_	3.0	-	pF	V _{CB} =10V, I _E = 0A, f=1MHz

•External dimensions (Unit : mm)



Inner circuit



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